

BKKT 273; BKKH 273



Thyristor / Diode Modules

BKKT 273

BKKH 273

Features

- Industrial standard package
- Electrically insulated base plate
- Heat transfer through aluminum oxide ceramic insulated metal base plate
- Chip soldered on direct copper bonded Al₂O₃ ceramic
- Thyristor with center gate
- UL recognition applied for file no. E63532

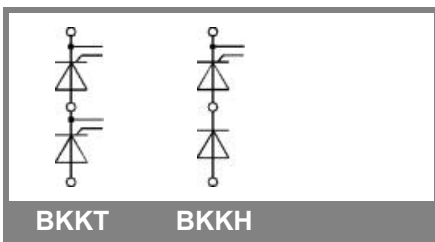
Typical Applications*

- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

1) See the assembly instructions

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_{TRMS} = 450$ A (maximum value for continuous operation) $I_{TAV} = 273$ A (sin. 180; $T_c = 85$ °C)	
1300	1200	BKKT 273/12E	BKKH 273/12E
1700	1600	BKKT 273/16E	BKKH 273/16E
1900	1800	BKKT 273/18E	BKKH 273/18E

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; $T_c = 85$ (100) °C;	273 (202)	A
I_{TSM}	$T_{vj} = 25$ °C; 10 ms $T_{vj} = 130$ °C; 10 ms	9000 8000	A A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms $T_{vj} = 130$ °C; 8,3 ... 10 ms	405000 320000	A ² s A ² s
V_T	$T_{vj} = 25$ °C; $I_T = 750$ A	max. 1,6	V
$V_{T(TO)}$	$T_{vj} = 130$ °C	max. 0,9	V
r_T	$T_{vj} = 130$ °C	max. 0,92	mΩ
I_{DD}, I_{RD}	$T_{vj} = 130$ °C; $V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 100	mA
t_{gd}	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/μs	1	μs
t_{gr}	$V_D = 0,67 * V_{DRM}$	2	μs
$(di/dt)_{cr}$	$T_{vj} = 130$ °C	max. 130	A/μs
$(dv/dt)_{cr}$	$T_{vj} = 130$ °C	max. 1000	V/μs
t_q	$T_{vj} = 130$ °C, typ.	150	μs
I_H	$T_{vj} = 25$ °C; typ. / max.	150 / 500	mA
I_L	$T_{vj} = 25$ °C; $R_G = 33$ Ω; typ. / max.	300 / 2000	mA
V_{GT}	$T_{vj} = 25$ °C; d.c.	min. 2	V
I_{GT}	$T_{vj} = 25$ °C; d.c.	min. 150	mA
V_{GD}	$T_{vj} = 130$ °C; d.c.	max. 0,25	V
I_{GD}	$T_{vj} = 130$ °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,104 / 0,052	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,108 / 0,054	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,122 / 0,061	K/W
$R_{th(c-s)}$	per thyristor / per module	0,08 / 0,04	K/W
T_{vj}		- 40 ... + 130	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 / 3000	V~
M_s	to heatsink	5 ± 15 % ¹⁾	Nm
M_t	to terminals	9 ± 15 %	Nm
a		$5 * 9,81$	m/s ²
m	approx.	410	g
Case	BKKT BKKH	A 43a A 56a	



BKKT

BKKH

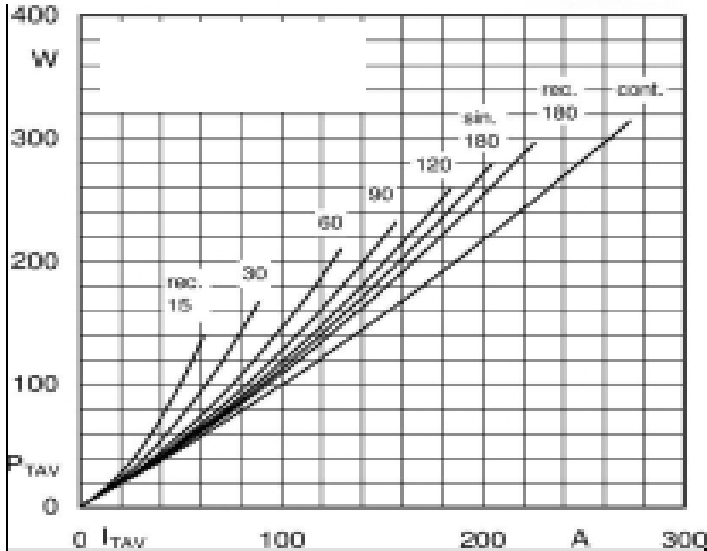


Fig. 1L Power dissipation per thyristor vs. on-state current

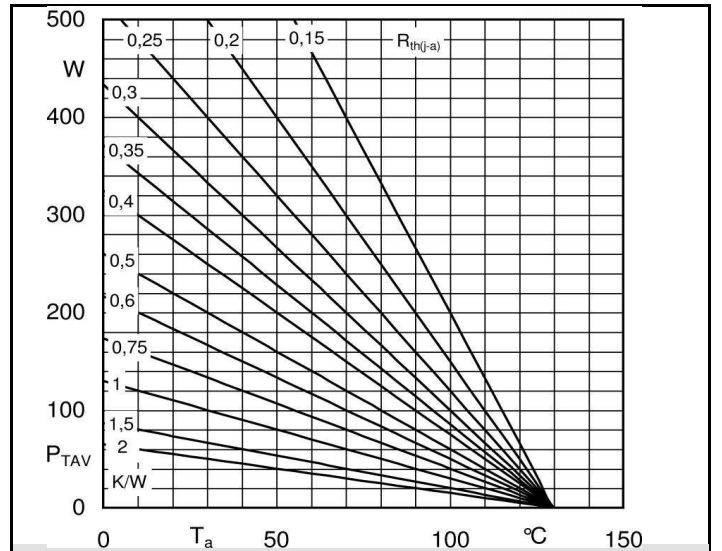


Fig. 1R Power dissipation per thyristor vs. ambient temp.

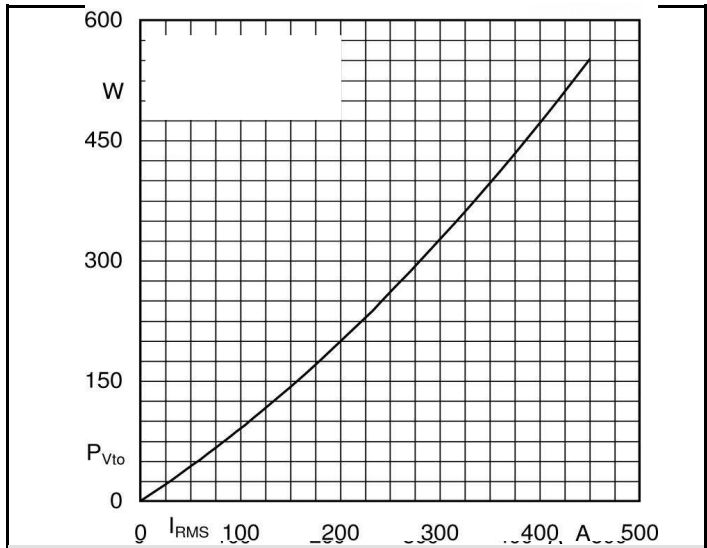


Fig. 2L Power dissipation per module vs. rms current

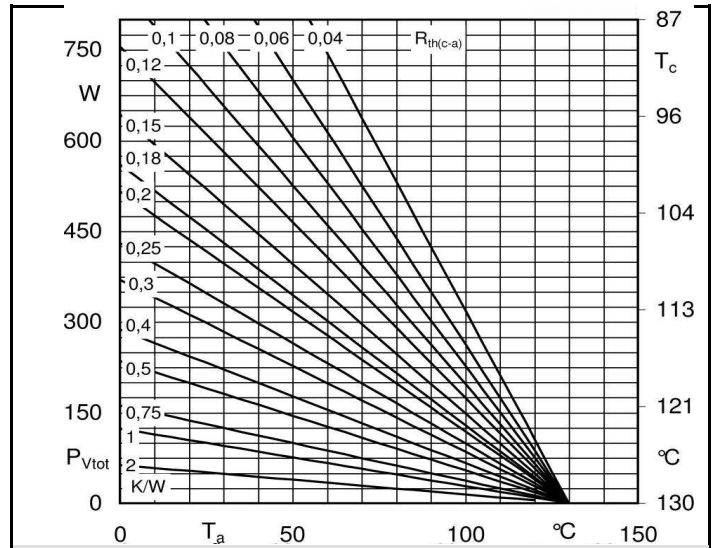


Fig. 2R Power dissipation per module vs. case temp.

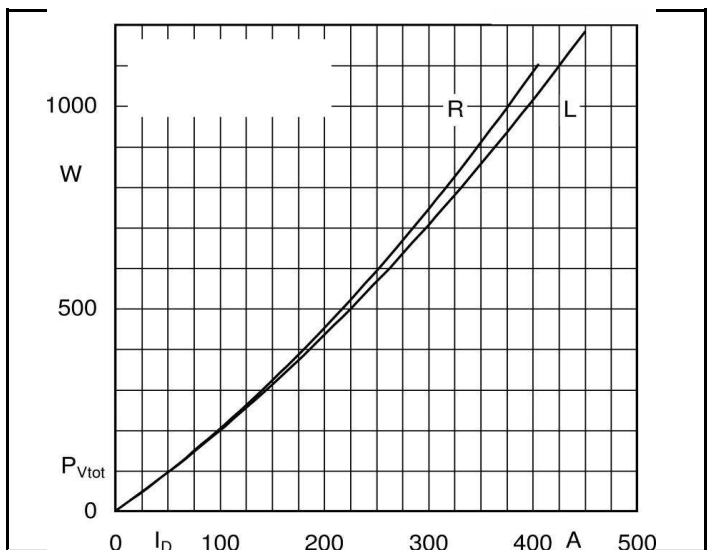


Fig. 3L Power dissipation of two modules vs. direct current

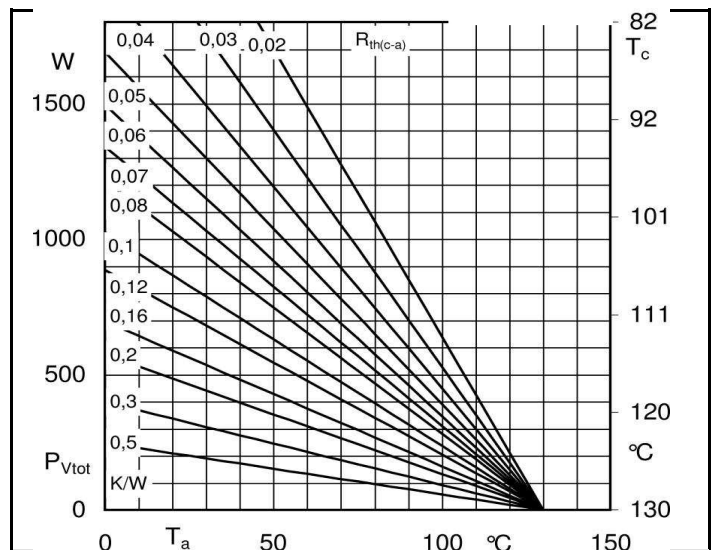
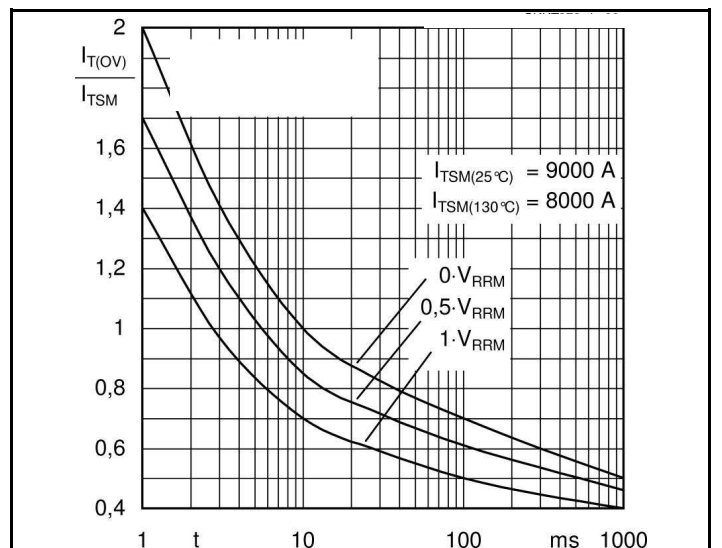
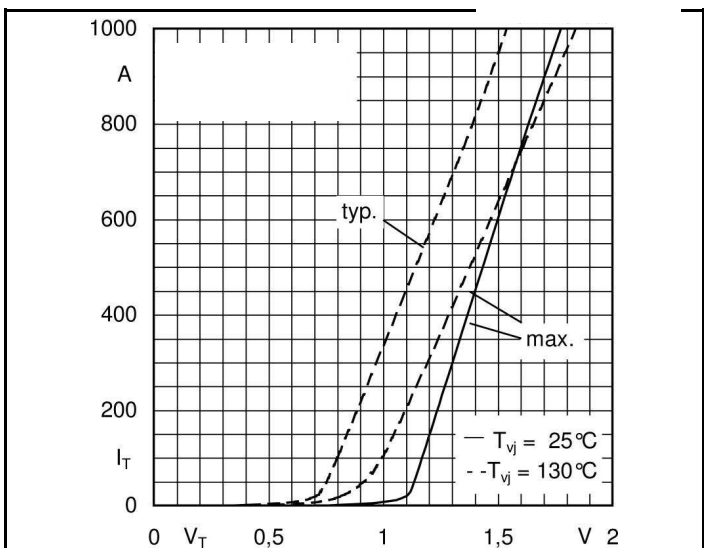
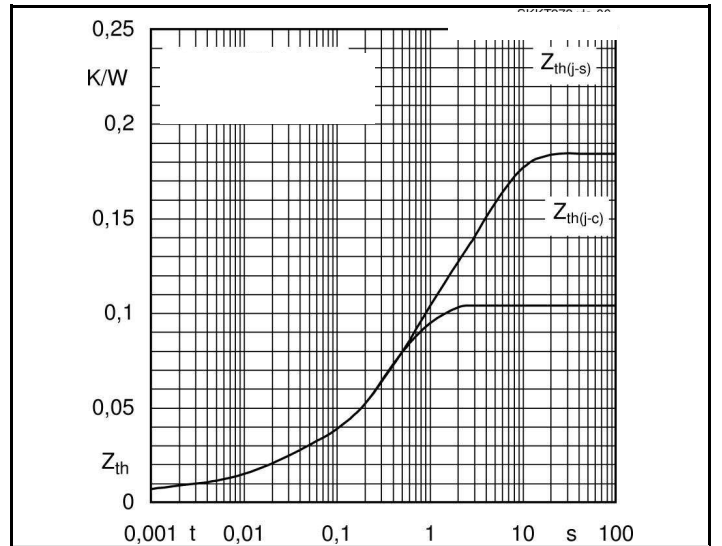
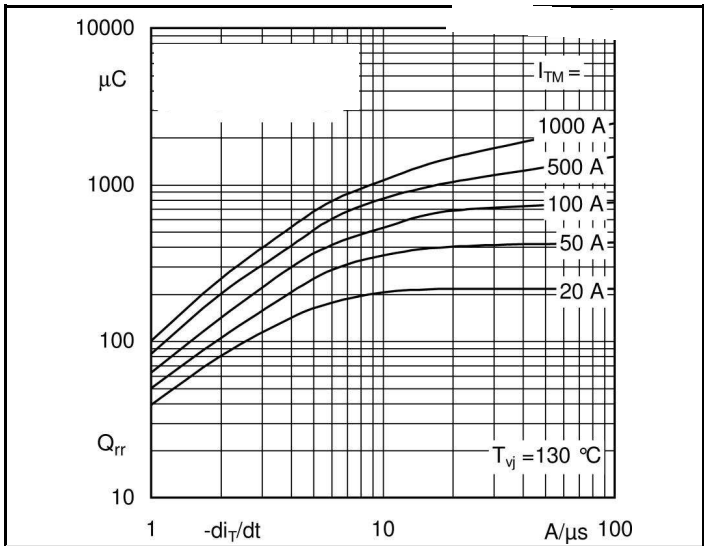
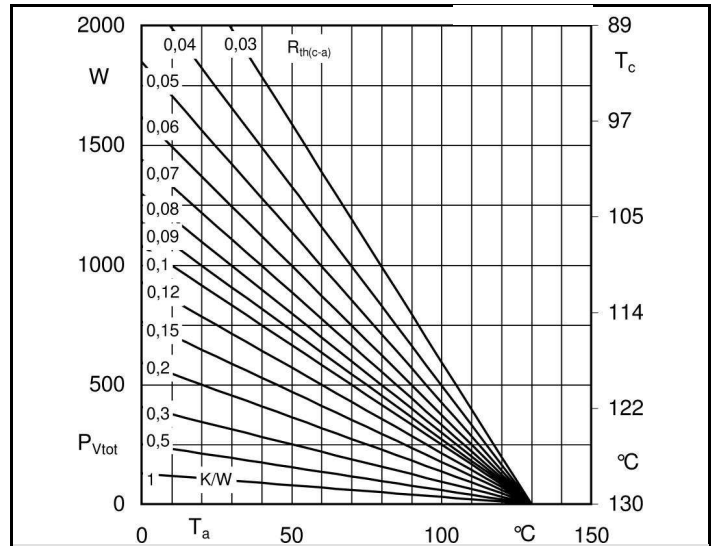
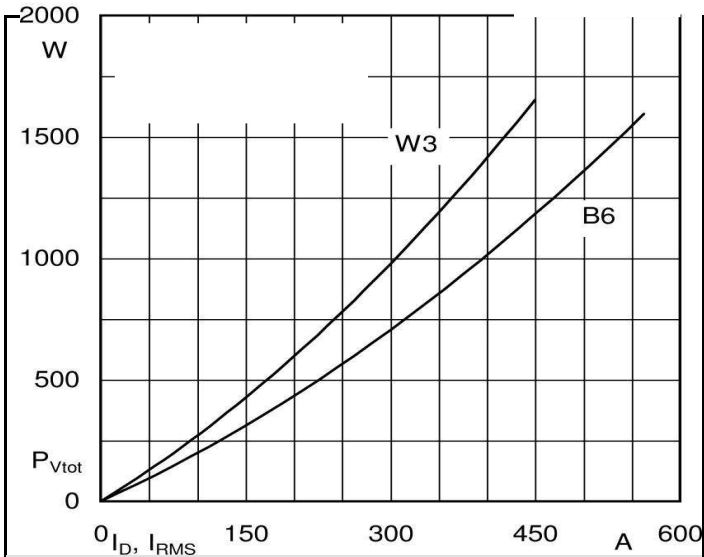


Fig. 3R Power dissipation of two modules vs. case temp.



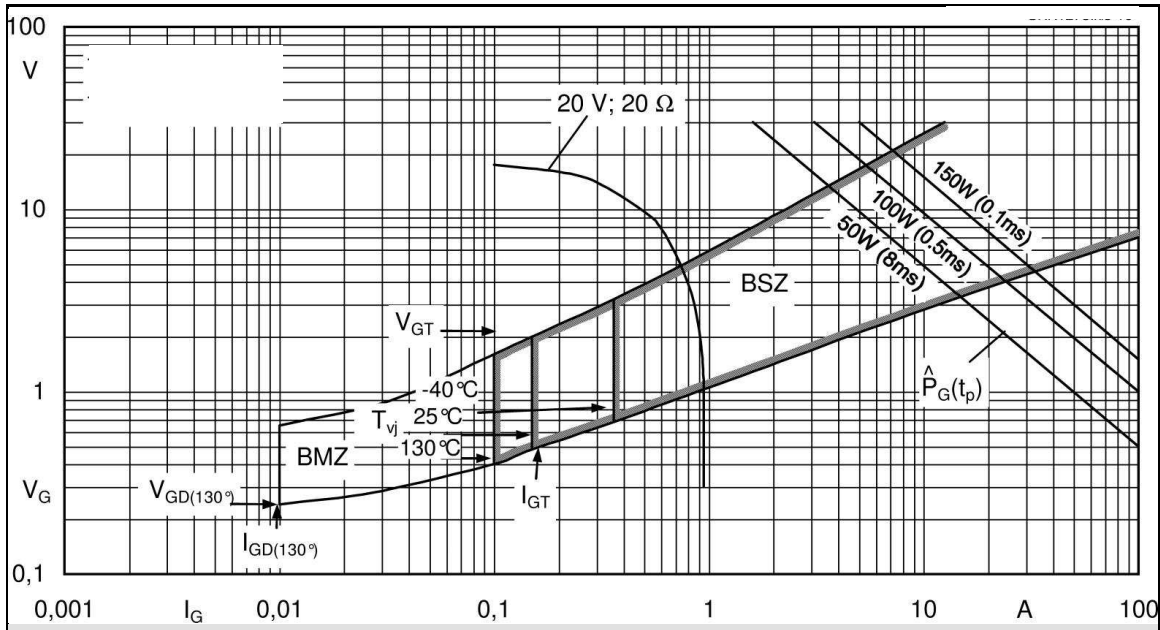
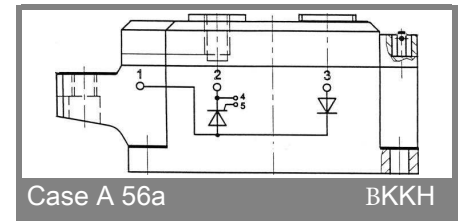
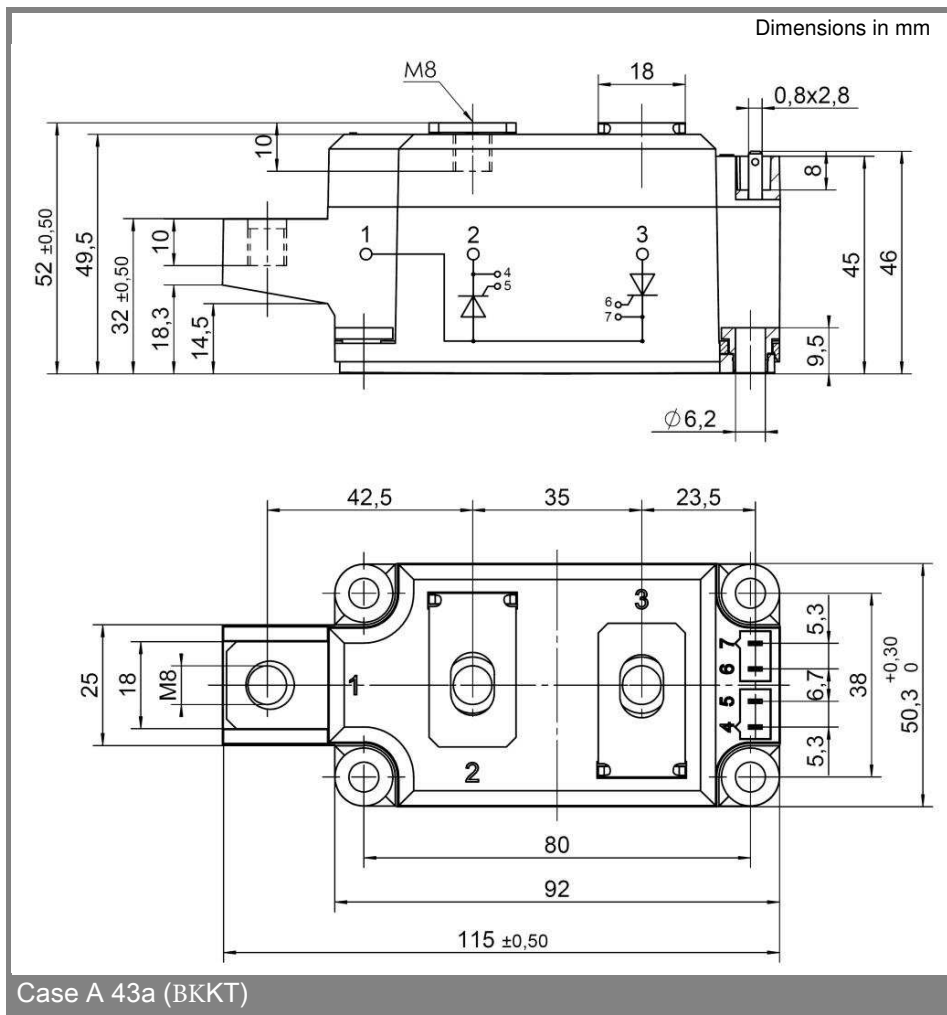


Fig. 9 Gate trigger characteristics



* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of products in life support appliances and systems is subject to prior specification and written approval by . We

therefore strongly recommend prior consultation of our personal.